## FAIRCHILD

## FDC6323L

## Integrated Load Switch

## General Description

These Integrated Load Switches are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage high side load switch application where low conduction loss and ease of driving are needed.

## Features

- $\mathrm{V}_{\text {DROP }}=0.2 \mathrm{~V} @ \mathrm{~V}_{\text {IN }}=5 \mathrm{~V}, \mathrm{I}_{\mathrm{L}}=1 \mathrm{~A}, \mathrm{~V}_{\text {ONOFF }}=1.5 \mathrm{~V}$ to 8 V $\mathrm{V}_{\text {DROP }}=0.3 \mathrm{~V} @ \mathrm{~V}_{\text {IN }}=3.3 \mathrm{~V}, \mathrm{I}_{\mathrm{L}}=1 \mathrm{~A}, \mathrm{~V}_{\text {ON OFFF }}=1.5 \mathrm{~V}$ to 8 V .
- High density cell design for extremely low on-resistance.
- $\mathrm{V}_{\text {ONOFF }}$ Zener protection for ESD ruggedness. >6KV Human Body Model.
- SuperSOT ${ }^{\text {TM }}-6$ package design using copper lead frame for superior thermal and electrical capabilities.

| SOT-23 | SuperSOT $^{\text {TM }-6 ~}$ | SuperSOT $^{\text {TM }}$-8 | SO-8 | SOT-223 |
| :---: | :---: | :---: | :---: | :---: |



SuperSOT ${ }^{T M}$ - 6


Absolute Maximum Ratings $T_{A}=25^{\circ} \mathrm{C}$ unless otherwise noted

| Symbol | Parameter | FDC6323L | Units |
| :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {IN }}$ | Input Voltage Range | 3-8 | V |
| $\mathrm{V}_{\text {ONOFF }}$ | On/Off Voltage Range | 1.5-8 | V |
| $\mathrm{I}_{\mathrm{L}}$ | Load Current @ $\mathrm{V}_{\text {DROP }}=0.5 \mathrm{~V}$ - Continuous (Note 1) <br> - Pulsed (Note 1\&3) | 1.5 2.5 | A |
| $\mathrm{P}_{\mathrm{D}}$ | Maximum Power Dissipation (Note 2a) | 0.7 | W |
| $\mathrm{T}_{\mathrm{J}}, \mathrm{T}_{\text {STG }}$ | Operating and Storage Temperature Range | -55 to 150 | ${ }^{\circ} \mathrm{C}$ |
| ESD | Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf/15000hm) | 6 | kV |

## THERMAL CHARACTERISTICS

| $\mathrm{R}_{\text {日JA }}$ | Thermal Resistance, Junction-to-Ambient | (Note 2a) | 180 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| :--- | :--- | :--- | :---: | :---: |
| $\mathrm{R}_{\theta \mathrm{OC}}$ | Thermal Resistance, Junction-to-Case | (Note 2) | 60 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Electrical Characteristics ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |  |  |
| $\mathrm{I}_{\text {FL }}$ | Forward Leakage Current | $\mathrm{V}_{\text {IN }}=8 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=0 \mathrm{~V}$ |  |  | 1 | $\mu \mathrm{A}$ |
| $\mathrm{I}_{\text {RL }}$ | Reverse Leakage Current | $\mathrm{V}_{\text {IN }}=-8 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=0 \mathrm{~V}$ |  |  | -1 | $\mu \mathrm{A}$ |

ON CHARACTERISTICS ${ }_{\text {(Note } 3)}$

| $\mathrm{V}_{\text {IN }}$ | Input Voltage |  | 3 |  | 8 | V |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {ONOFF }}$ | On/Off Voltage |  | 1.5 |  | 8 | V |
| $\mathrm{V}_{\text {DROP }}$ | Conduction Voltage Drop @ 1A | $\mathrm{V}_{\text {IV }}=5 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=3.3 \mathrm{~V}$ |  | 0.145 | 0.2 | V |
|  |  | $\mathrm{V}_{\text {IV }}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=3.3 \mathrm{~V}$ |  | 0.178 | 0.3 |  |
| L | Load Current | $\mathrm{V}_{\text {DROP }}=0.2 \mathrm{~V}, \mathrm{~V}_{\text {IN }}=5 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=3.3 \mathrm{~V}$ | 1 |  |  | A |
|  |  | $\mathrm{V}_{\text {DROP }}=0.3 \mathrm{~V}, \mathrm{~V}_{\text {IV }}=3.3 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=3.3 \mathrm{~V}$ | 1 |  |  |  |

Notes:

1. $\mathrm{V}_{\text {IN }}=8 \mathrm{~V}, \mathrm{~V}_{\text {ONOFF }}=8 \mathrm{~V}, \mathrm{~V}_{\text {DROP }}=0.5 \mathrm{~V}, \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$
2. $R_{\theta J \mathrm{~A}}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\text {eJC }}$ is guaranteed by design while $R_{\theta C A}$ is determined by the user's board design.
$P_{D}(t)=\frac{T_{J}-T_{A}}{R_{\theta J A}(t)}=\frac{T_{J}-T_{A}}{R_{\theta J} C^{+} R_{\theta C A}(t)}=I_{D}^{2}(t) \times R_{D S(O N) @ T_{J}}$
Typical $R_{\text {EJA }}$ for single device operation using the board layouts shown below on FR-4 PCB in a still air environment:
a. $180^{\circ} \mathrm{C} / \mathrm{W}$ when mounted on a 2 oz minimum copper pad.

3. Pulse Test: Pulse Width $\leq 300 \mu \mathrm{~s}$, Duty Cycle $\leq 2.0 \%$

Typical Electrical Characteristics $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)


Figure 1. $\mathrm{V}_{\mathrm{DROP}}$ Versus $\mathrm{I}_{\mathrm{L}}$ at $\mathrm{V}_{\mathrm{IN}}=5 \mathrm{~V}$.


Figure 3. $\mathrm{V}_{\text {DROP }}$ Versus $\mathrm{V}_{\mathrm{IN}}$ at $\mathrm{I}_{\mathrm{L}}=1 \mathrm{~A}$.


Figure 5. On Resistance Variation with Input Voltage. , Volat


Figure 2. $\mathrm{V}_{\mathrm{DROP}}$ Versus $\mathrm{I}_{\mathrm{L}}$ at $\mathrm{V}_{\mathrm{IN}}=3.3 \mathrm{~V}$.


Figure 4. $R_{(O N)}$ Versus $I_{L}$ at $V_{I N}=3.3 V$.

Typical Electrical Characteristics $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)


Figure 6. Switching Variation with R2 at Vin $=5 \mathrm{~V}$ and $\mathrm{R} 1=20 \mathrm{KOhm}$.


Figure 8. Switching Variation with R2 at $\mathrm{Vin}=2.5 \mathrm{~V}$ and $\mathrm{R} 1=20 \mathrm{KOhm}$.


Figure 10. Vdrop Variation with Vin and R2.


Figure 7. Switching Variation with R2 at $\mathrm{Vin}=3.3 \mathrm{~V}$ and $\mathrm{R} 1=20 \mathrm{KOhm}$.


Figure 9. \% of Current Overshoot Variation with Vin and R2.


Figure 11. Switching Waveforms.

Typical Electrical Characteristics $\left(T_{A}=25^{\circ} \mathrm{C}\right.$ unless otherwise noted)


Figure 12. Safe Operating Area.


Figure 13. Transient Thermal Response Curve.
Note: Thermal characterization performed on the conditions described in Note 2a.
Transient thermal response will change depends on the circuit board design.

## FDC6323L Load Switch Application



## General Description

This device is particularly suited for compact computer peripheral switching applications where 8 V input and 1 A output current capability are needed. This load switch integrates a small N-Channel Power MOSFET (Q1) which drives a large P-Channel Power MOSFET (Q2) in one tiny SuperSOT ${ }^{\mathrm{TM}}$-6 package.

A load switch is usually configured for high side switching so that the load can be isolated from the active power source. A P-Channel Power MOSFET, because it does not require its drive voltage above the input voltage, is usually more cost effective than using an N -Channel device in this particular application. A large P-Channel Power MOSFET minimizes voltage drop. By using a small N -Channel device the driving stage is simplified.

## Component Values

| R1 | Typical $10 \mathrm{k}-1 \mathrm{M} \Omega$ |  |
| :--- | :--- | :--- |
| R2 | Typical $0-100 \mathrm{k} \Omega$ | (optional) |
| C1 | Typical 1000 pF | (optional) |

## Design Notes

- R1 is needed to turn off Q2.
- R2 can be used to soft start the switch in case the output capacitance Co is small.
- R2 should be at least 10 times smaller than R1 to guarantee Q1 turns on.
- By using R1 and R2 a certain amount of current is lost from the input. This bias current loss is given by the equation
$I_{\text {BIAS_LOSS }}=\frac{V \text { Vin }}{R 1+R 2}$ when the switch is ON. $I_{\text {BIAS_LOSS }}$ can be minimized by selecting a large value for R1.
- R2 and $\mathrm{C}_{\text {RSS }}$ of Q2 make ramp for slow turn on. If excessive overshoot current occurs due to fast turn on, additional capacitance C 1 can be added externally to slow down the turn on.


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| CROSSVOLT ${ }^{\text {™ }}$ | РОРтм | VCX ${ }^{\text {™ }}$ |
| $\mathrm{E}^{2} \mathrm{CMOS}^{\text {M }}$ | PowerTrench ${ }^{\text {TM }}$ |  |
| FACT ${ }^{\text {т }}$ | QFET ${ }^{\text {TM }}$ |  |
| FACT Quiet Series ${ }^{\text {™ }}$ | QS ${ }^{\text {TM }}$ |  |
| FAST ${ }^{\circledR}$ | Quiet Series ${ }^{\text {TM }}$ |  |
| FASTr ${ }^{\text {TM }}$ | SuperSOT ${ }^{\text {TM }}$-3 |  |
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| HiSeC ${ }^{\text {¹ }}$ | SuperSOT™-8 |  |

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